

# EH2525ETTS-64.000M TR [Click part number to visit Part Number Details page](#)

## REGULATORY COMPLIANCE (Data Sheet downloaded on Dec 6, 2018)



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## ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) HCMOS/TTL (CMOS) 5.0Vdc 4 Pad 5.0mm x 7.0mm Ceramic Surface Mount (SMD) 64.000MHz  $\pm 25$ ppm -40°C to +85°C

## ELECTRICAL SPECIFICATIONS

Nominal Frequency	64.000MHz
Frequency Tolerance/Stability	$\pm 25$ ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	$\pm 5$ ppm/year Maximum
Operating Temperature Range	-40°C to +85°C
Supply Voltage	5.0Vdc $\pm 10\%$
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOL= +16mA)
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 $\pm 10$ (%) (Measured at 1.4Vdc with TTL Load; Measured at 50% of waveform with HCMOS Load)
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	$\pm 250$ pSec Maximum, $\pm 100$ pSec Typical
One Sigma Clock Period Jitter	$\pm 50$ pSec Maximum, $\pm 30$ pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

## ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

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### MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	64.000M
3	XXXXX XXXXX=Ecliptek Manufacturing Identifier

### Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1

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## OUTPUT WAVEFORM & TIMING DIAGRAM

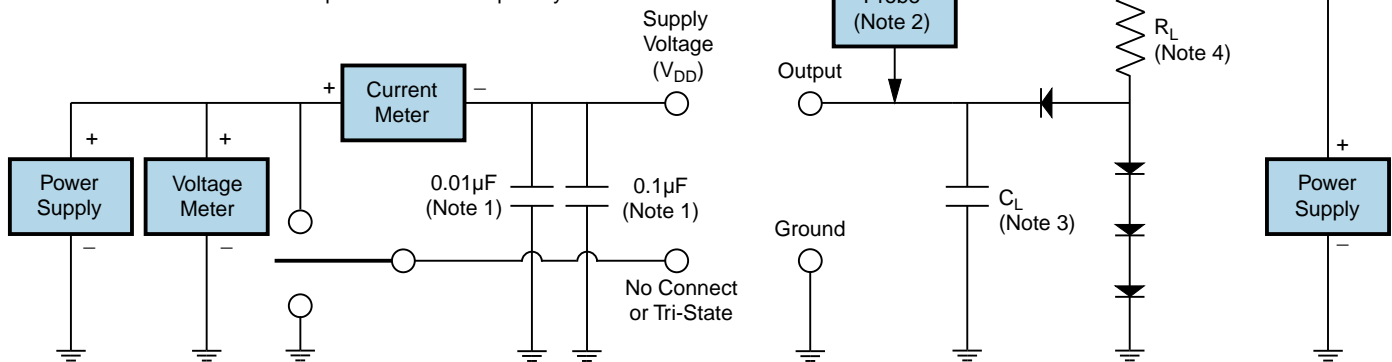


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## Test Circuit for TTL Output

Output Load Drive Capability	$R_L$ Value (Ohms)	$C_L$ Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1:  $R_L$  Resistance Value and  $C_L$  Capacitance Value Vs. Output Load Drive Capability



Note 1: An external  $0.1\mu\text{F}$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu\text{F}$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance ( $<12\text{pF}$ ), 10X attenuation factor, high impedance ( $>10\text{Mohms}$ ), and high bandwidth ( $>300\text{MHz}$ ) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

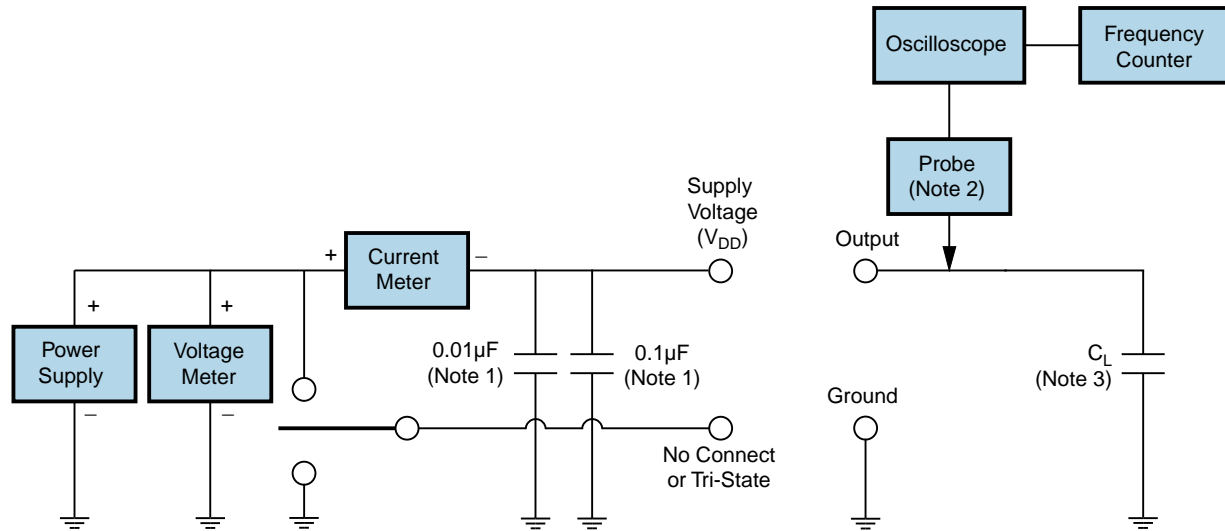
Note 4: Resistance value  $R_L$  is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

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## Test Circuit for CMOS Output



Note 1: An external  $0.1\mu\text{F}$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu\text{F}$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance ( $<12\text{pF}$ ), 10X attenuation factor, high impedance ( $>10\text{Mohms}$ ), and high bandwidth ( $>300\text{MHz}$ ) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

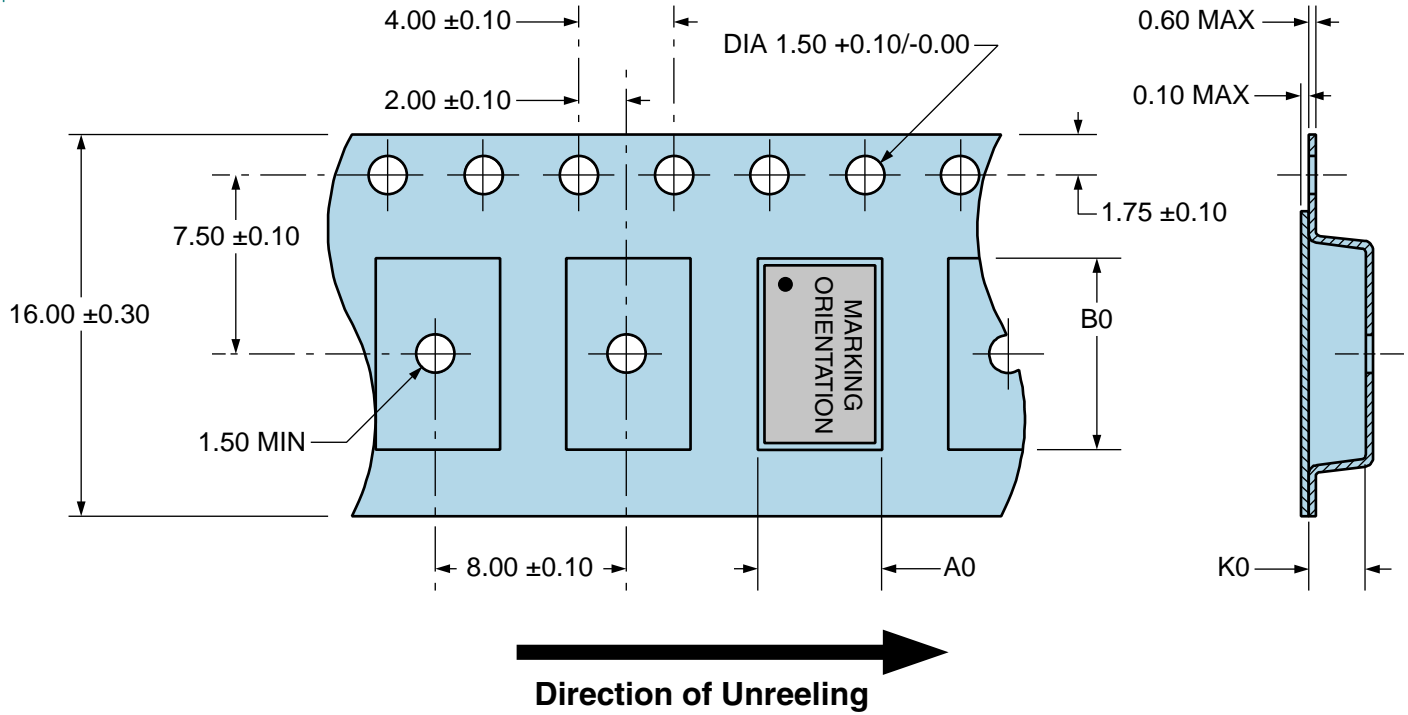
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## Tape & Reel Dimensions

Quantity Per Reel: 1,000 units

All Dimensions in Millimeters

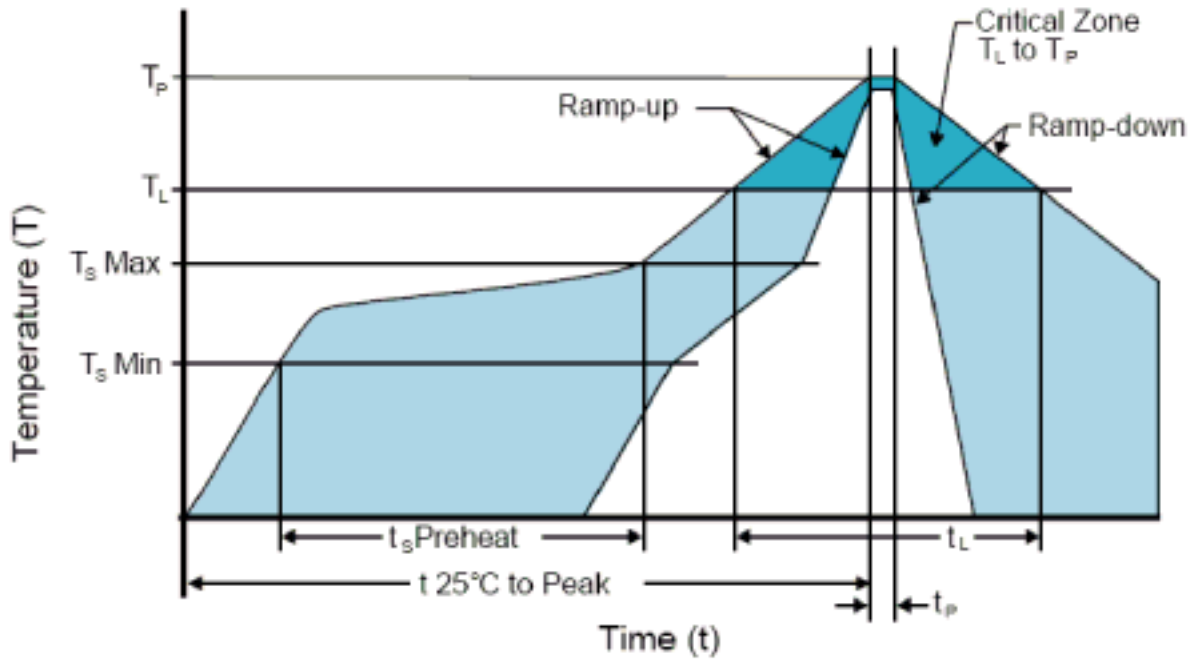
Compliant to EIA-481



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## Recommended Solder Reflow Methods



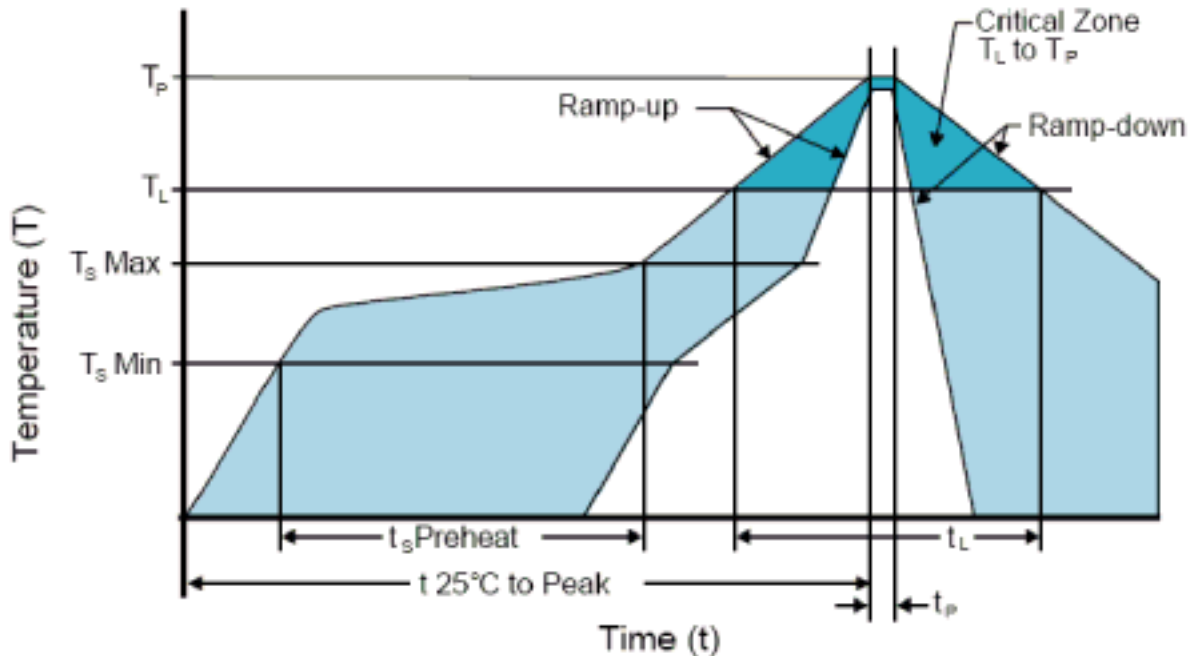
### High Temperature Infrared/Convection

<b><math>T_s</math> MAX to <math>T_L</math> (Ramp-up Rate)</b>	3°C/Second Maximum
<b>Preheat</b>	
- Temperature Minimum ( $T_s$ MIN)	150°C
- Temperature Typical ( $T_s$ TYP)	175°C
- Temperature Maximum ( $T_s$ MAX)	200°C
- Time ( $t_s$ MIN)	60 - 180 Seconds
<b>Ramp-up Rate (<math>T_L</math> to <math>T_P</math>)</b>	3°C/Second Maximum
<b>Time Maintained Above:</b>	
- Temperature ( $T_L$ )	217°C
- Time ( $t_L$ )	60 - 150 Seconds
<b>Peak Temperature (<math>T_P</math>)</b>	260°C Maximum for 10 Seconds Maximum
<b>Target Peak Temperature (<math>T_P</math> Target)</b>	250°C +0/-5°C
<b>Time within 5°C of actual peak (<math>t_p</math>)</b>	20 - 40 Seconds
<b>Ramp-down Rate</b>	6°C/Second Maximum
<b>Time 25°C to Peak Temperature (t)</b>	8 Minutes Maximum
<b>Moisture Sensitivity Level</b>	Level 1
<b>Additional Notes</b>	Temperatures shown are applied to body of device.

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## Recommended Solder Reflow Methods



### Low Temperature Infrared/Convection 240°C

$T_s$ MAX to $T_L$ (Ramp-up Rate)	5°C/Second Maximum
<b>Preheat</b>	
- Temperature Minimum ( $T_s$ MIN)	N/A
- Temperature Typical ( $T_s$ TYP)	150°C
- Temperature Maximum ( $T_s$ MAX)	N/A
- Time ( $t_s$ MIN)	60 - 120 Seconds
<b>Ramp-up Rate (<math>T_L</math> to <math>T_P</math>)</b>	5°C/Second Maximum
<b>Time Maintained Above:</b>	
- Temperature ( $T_L$ )	150°C
- Time ( $t_L$ )	200 Seconds Maximum
<b>Peak Temperature (<math>T_P</math>)</b>	240°C Maximum
<b>Target Peak Temperature (<math>T_P</math> Target)</b>	240°C Maximum 2 Times / 230°C Maximum 1 Time
<b>Time within 5°C of actual peak (<math>t_P</math>)</b>	10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time
<b>Ramp-down Rate</b>	5°C/Second Maximum
<b>Time 25°C to Peak Temperature (t)</b>	N/A
<b>Moisture Sensitivity Level</b>	Level 1
<b>Additional Notes</b>	Temperatures shown are applied to body of device.

### Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)